Docket No.

OCT 0 3 2006

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Frederic MAZEN, et al

292759US0PC

SERIAL NO: 10/584,053

GAU:

FILED: June 22, 2006

EXAMINER:

FOR: METHOD FOR THE ORGANISED GROWTH OF NANOSTRUCTURES

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS

ALEXANDRIA, VIRGINIA 22313

SIR.

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-149C. Oppies of the listed references are attached, where required, as are either attements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in any communication
 from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of
 this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filling of this statement.

DEPOSIT ACCOUNT

■ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

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Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03) Registration No. 24,618

Surinder Sachar Registration No. 34,423

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Form PTO 1449 U.S. CAPARTMENT OF COMMERCE PATE AND TRADEMARK CHICE			ATTY DOCKET NO. 292759USOPCT			SERIAL NO. 10/584,053			
		PADE	MATERIA	APPLICANT 10/304,033					
LIST OF REFERENCES CITED BY APPLICANT Frederic MAZEN, et al.									
				FILING DATE	-	GROUP			
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EXAMINER	$\overline{}$	DOCUMENT	DATE	NAME	CLASS	SUB		FILING DATE	
INITIAL	-	NUMBER	08/10/1999	TADA et al.	CLASS	CLASS		APPROPRIATE	
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	AU	GERLACH R., "FOCUSED ION BEAM METHODS OF NANOFABRICATION: ROOM AT THE BOTTOM", PROCEEDINGS OF SPIE, Vol. 4510, pages 96-106, XP 008035414, 2001							
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	AW	BARON T. et al., "SILICON QUANTUM DOT NUCLEATION ON SI3 N4, SIO2, AND SIOx NY SUBSTRATES FOR NANOELECTRONIC DEVICES", JOURNAL OF CRYSTAL GROWTH, Vol. 209, pages 1004-1008, 2000							
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	AY								
	AZ				Addi	tional Refe	rences	sheet(s) attached	
Examiner	/Joseph Mille		Date Considered 01/13/2009						
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

U.S. PCT Application Serial No: 10/584,053

Filed: June 22, 2006 Frederic MAZEN, et al. Docket No. 292759 US

STATEMENT OF RELEVANCY

- References AA-AD & AT-AU have been cited in the International Search Report.
 A copy of these references is being submitted herewith.
- References have been cited in the corresponding copy of these references is being submitted herewith.
- 3) References AV-AX are discussed in the specification. A copy of these references is being submitted herewith.
- 4) References are additional prior art known to Applicant. A copy of these references is being submitted herewith.